RF Nonlinear Device Characterization Yields Improved Modeling Accuracy

M.A. Smith, T.S. Howard, K.J. Anderson and A.M. Pavio. "RF Nonlinear Device Characterization Yields Improved Modeling Accuracy." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 381-384.

A new method for measuring the nonlinear characteristics of microwave GaAs field-effect transistors (FETs) has been developed and evaluated. The technique, which involves RF rather than DC FET measurement, has yielded significant improvement in circuit compression point and harmonic content modeling accuracy.

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